

DSs

Browse

Clear

US:PGPUB;USPAT;EPO;JPO;DERWENT;ISM;TDB

Plurals

Default operator: OR

Highlight all hit terms initially

S41 and S30

Nov 2004

BRS form

ISAR form

Image

Text

HTML

	U	Inventor	Document#	Issue	P	Title	Current	Current XR	Retrieval	S	C	P	Image	Doc	P
1	<input type="checkbox"/>	Fan, Der-Tsyr	US 2004013	200403		Flash memory with trench select gate and fa	365/185	365/51		<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 200401	
2	<input type="checkbox"/>	Sakui, Koji et	US 6577533	200305		Nonvolatile semiconductor memory and meth	365/185	257/317; 2		<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 657753	
3	<input type="checkbox"/>	Prall, Kirk	US 6759707	200402		2F2 memory device system	257/315	257/314		<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 675970	
4	<input type="checkbox"/>	Harari, Eliyah	US 2004021	200401		Non-volatile memory cells utilizing substrate	257/315			<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 200402	
5	<input checked="" type="checkbox"/>	Chang, Ko-Hs	US 2004019	200401		ISPLIT GATE FLASH MEMORY CELL AND M	438/266			<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 200401	
6	<input checked="" type="checkbox"/>	Hsu, Cheng-Y	US 2004018	200401		Flash memory device with selective gate wit	257/316			<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 200401	
7	<input checked="" type="checkbox"/>	Prall, Kirk	US 2004014	200402		2F2 memory device	365/145	257/E21.68		<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 200401	
8	<input checked="" type="checkbox"/>	Yamauchi, Yo	US 2004010	200401		Nonvolatile semiconductor memory and meth	365/185			<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 200401	
9	<input checked="" type="checkbox"/>	Chen, Chiou-F	US 2004005	200404		Self-aligned split-gate NAND flash memory a	365/185			<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 200400	
10	<input checked="" type="checkbox"/>	Harari, Eliyah	US 2004000	200402		Non-volatile memory cells utilizing substrate	257/315	257/316		<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 200400	

File Details HTML

Ready

3/1/04